



RECTRON

SEMICONDUCTOR

TECHNICAL SPECIFICATION

BAW56

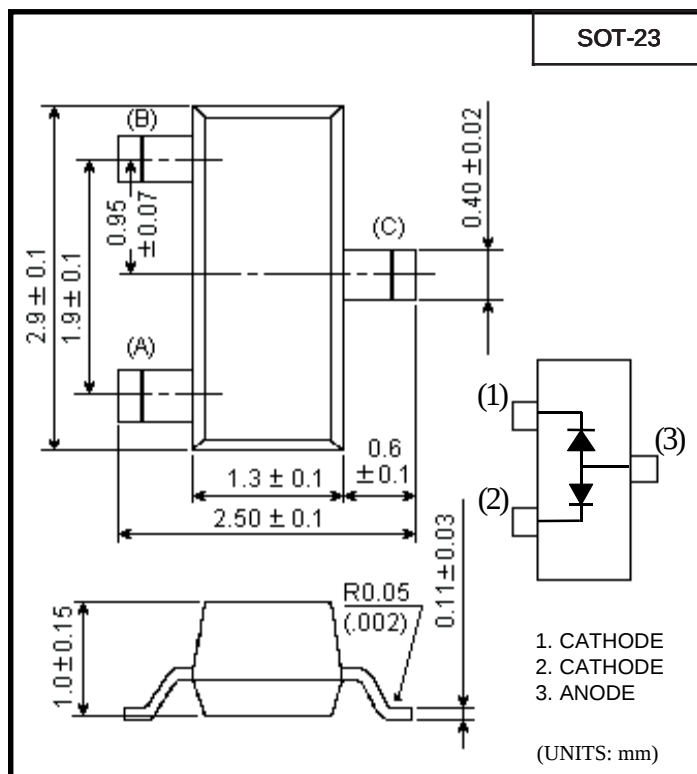
SURFACE MOUNT, DUAL 1N4148 COMMON ANODE DIODE

Absolute Maximum Ratings (Ta=25°C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VRRM	85	V
Reverse Recovery Time	trr	4	ns
Forward Voltage @ If = 50 mA	VF	1.0	V
Forward Current	IF	215	mA
Junction Temp.	Tj	-55 to 150	°C
Storage Temp.	Tstg	-55 to 150	°C

Mechanical Data

Items	Materials
Package	SOT-23
Lead Frame	42 Alloy
Lead Finish	Solder Plating
Bond Wire	Au
Mold Resin	Epoxy
Chip	Silicon



Electrical Characteristics per Diode (Ta=25°C)

Ratings	Symbol	Ratings	Unit
Reverse Breakdown Voltage IR= 100uA	VBR	75	V
Repetitive Peak Reverse Voltage	VRRM	85	V
Repetitive Peak Forward Current	IFRM	450	mA
Forward Voltage IF= 1mA IF= 10mA IF= 50mA IF= 150mA	VF	715 855 1000 1250	mV
Reverse Current VR= 75V VR= 25V (Tj= 150°C) VR= 75V (Tj= 150°C)	IR	1.0 30 50	uA
Junction Capacitance VR = 0 V, f = 1MHz	Cj	2.0	pF
Reverse Recovery Time IF= IR= 10mA; RL= 100 ohms	trr	4	ns
Thermal Resistance (junction to ambient)	RθJA	500	°C/W

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